

General Purpose Transistors

NPN Bipolar Junction Transistor

(Complementary PNP Device: MMBT2131T1/T3)

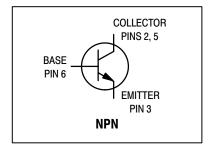
MMBT2132T1 MMBT2132T3

0.7 AMPERES 30 VOLTS – V(BR)CEO 342 mW

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

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Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	30	V
Collector–Base Voltage	V _{CBO}	40	V
Emitter–Base Voltage	VEBO	5.0	V
Collector Current	IC	700	mA
Base Current	ΙΒ	350	mA
Total Power Dissipation @ T _C = 25°C Total Power Dissipation @ T _C = 85°C Thermal Resistance – Junction to Ambient (1)	P _D P _D R _θ JA	342 178 366	mW mW °C/W
Total Power Dissipation @ T _C = 25°C Total Power Dissipation @ T _C = 85°C Thermal Resistance – Junction to Ambient (2)	P _D P _D R _θ JA	665 346 188	mW mW °C/W
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C





ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characte	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS				•		
Collector-Base Breakdown Voltage	$(I_C = 100 \mu\text{Adc})$	V(BR)CBO	40	-	-	Vdc
Collector–Emitter Breakdown Voltage	(I _C = 10 mAdc)	V(BR)CEO	30	-	_	Vdc
Emitter-Base Breakdown Voltage	(I _E = 100 μAdc)	V(BR)EBO	5.0	-	_	Vdc
Collector Cutoff Current (VC	(V _{CB} = 25 Vdc, I _E = 0 Adc) B = 25 Vdc, I _E = 0 Adc, T _A = 125°C)	ICBO	-	-	1.0 10	μAdc
Emitter Cutoff Current	(V _{EB} = 5.0 Vdc, I _C = 0 Adc)	I _{EBO}	_	-	10	μAdc
ON CHARACTERISTICS				•		
DC Current Gain	$(V_{CE} = 3.0 \text{ Vdc}, I_{C} = 100 \text{ mAdc})$	hFE	150	_	_	Vdc
Collector–Emitter Saturation Voltage	$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	V _{CE(sat)}	_	_	0.25	Vdc
Collector–Emitter Saturation Voltage	(I _C = 700 mAdc, I _B = 70 mAdc)	V _{CE(sat)}	_	-	0.4	Vdc
Base–Emitter Saturation Voltage	(I _C = 700 mAdc, I _B = 70 mAdc)	V _{BE(sat)}	_	-	1.1	Vdc
Collector–Emitter Saturation Voltage	(I _C = 700 mAdc, V _{CE} = 1.0 Vdc)	V _{BE(on)}	_	_	1.0	Vdc

- 1. Minimum FR-4 or G-10 PCB, Operating to Steady State.
- 2. Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.

MMBT2132T1 MMBT2132T3

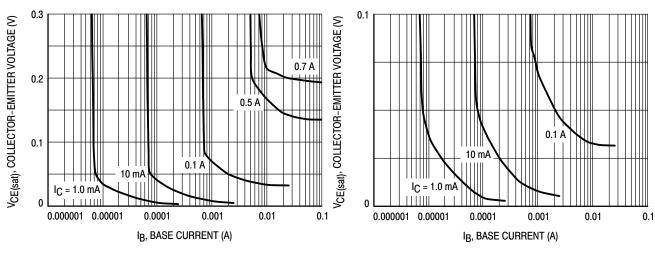


Figure 1. Collector Saturation Region

Figure 2. Collector Saturation Region

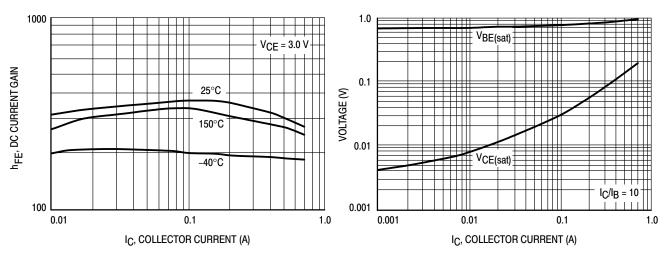


Figure 3. DC Current Gain

Figure 4. "ON" Voltages

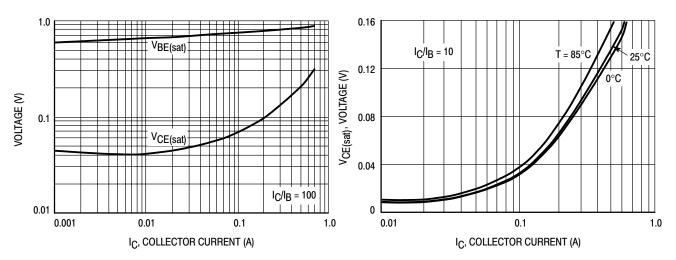


Figure 5. "ON" Voltages

Figure 6. Collector-Emitter Saturation Voltage

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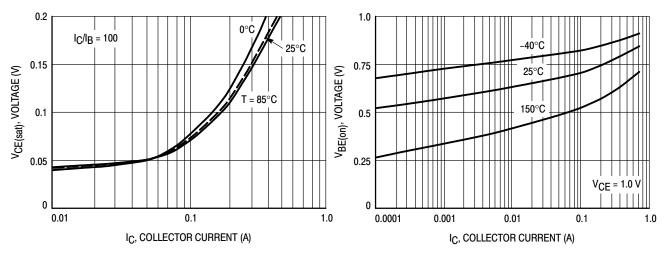


Figure 7. Collector-Emitter Saturation Voltage

Figure 8. VBE(on) Voltage

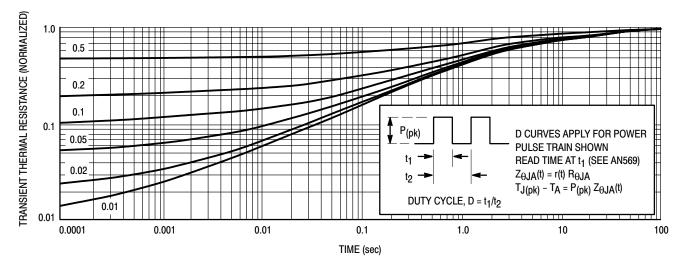
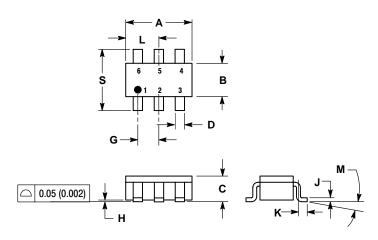


Figure 9. Thermal Response Curve

MMBT2132T1 MMBT2132T3

PACKAGE DIMENSIONS

SC-74 CASE 318F-03 **ISSUE F**



- STYLE 2: PIN 1. NO CONNECTION
 - 2. COLLECTOR 3. EMITTER

 - 4. NO CONNECTION
 - 5. COLLECTOR

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318F-01 AND -02 OBSOLETE. NEW STANDARD 318F-03.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1142	0.1220	2.90	3.10
В	0.0512	0.0669	1.30	1.70
С	0.0354	0.0433	0.90	1.10
D	0.0098	0.0197	0.25	0.50
G	0.0335	0.0413	0.85	1.05
Н	0.0005	0.0040	0.013	0.100
J	0.0040	0.0102	0.10	0.26
K	0.0079	0.0236	0.20	0.60
L	0.0493	0.0649	1.25	1.65
M	0 °	10°	0 °	10°
S	0.0985	0.1181	2.50	3.00

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